

Amendments to the Specification:

Please replace the title beginning at page 1, line 1, with the following amended title:

**METHOD OF ~~MANUFACTURING SEMICONDUCTOR DEVICE~~ MAKING A THIN FILM
TRANSISTOR USING LASER ANNEALING**

Please add the following new paragraph after the paragraph ending at page 14, line 16:

Fig. 24 shows an example of a laser annealing method of the present invention when the reflecting surface of the reflector is made to be a curved surface.

Please replace the paragraph beginning at page 20, line 3, with the following amended paragraph:

With respect to the laser light transmitted through the cylindrical lens 207, it forms an incidence angle of 45° to 90° relative to the surface of the substrate in a condensing process thereof. Thus, the second laser light 314 can be diffracted to reach the rear surface side of the semiconductor film and irradiated thereon. Also, when rugged portions are formed on the reflecting surface of the reflector 312 to effect diffuse reflection of the laser light, the second laser light 314 can be obtained more efficiently. [[When]] As shown, for example, in Fig. 24, when the reflecting surface of the reflector 312 is made to be a curved surface (for example, a concave surface), the laser light can be irradiated onto the semiconductor film while being condensed, and thus it is efficient.